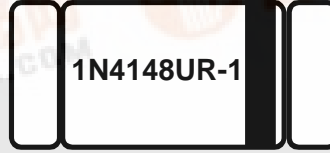


MINI-MELF-SMD



Silicon Diode

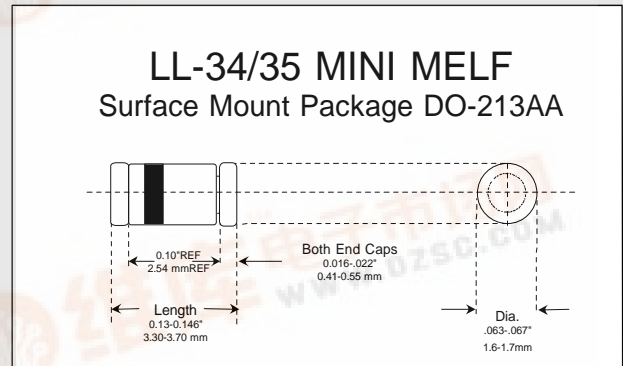
Applications

Switching

Used in general purpose applications, where a low current controlled forward characteristic and fast switching speed are important.

Features

- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond™ plating for problem free solderability
- Available in DO-35 package
- Approved to Mil-S-19500/116



Maximum Ratings	Symbol	Value	Unit
Peak Inverse Voltage	PIV	100 (Min.)	Volts
Average Rectified Current	I_{Avg}	200	mAmps
Continuous Forward Current	I_{Edc}	400	mAmps
Peak Surge Current ($t_{peak} = 1 \text{ sec.}$)	I_{peak}	0.5	Amp
Power Dissipation @ Endcap Temp. = 25 °C	P_{tot}	500	mWatts
Storage & Operating Temperature Range	$T_{St \& Op}$	-65 to +200	°C

Electrical Characteristics @ 25 °C*	Symbol	Absolute Limits	Unit
Forward Voltage Drop @ $I_F = 10 \text{ mA}$	V_F	1.0	Volts
Reverse Leakage Current @ $V_R = 20 \text{ V}$	I_R	0.025	μA
Breakdown Voltage @ $I_R = 5 \mu\text{A}$	PIV	75 (MIN)	Volts
Breakdown Voltage @ $I_R = 100\mu\text{A}$	PIV	100 (MIN)	Volts
Reverse Leakage Current @ $V_R = 20 \text{ V}$	I_R	0.025 (MAX)	μA
Reverse Leakage ($V_r = 20 \text{ V}, 150 \text{ }^\circ\text{C}$)	I_R	50 (MAX)	μA
Capacitance @ $V_R = 0 \text{ V}, f = 1\text{MHz}$	C_T	4.0 (MAX)	pF
Reverse Recovery Time (note 1)	t_{rr}	4.0 (MAX)	nSecs

Note 1: $I_F = 10 \text{ mA}, R_L = 100 \text{ Ohms}, V_r = 6.0 \text{ Volts}, I_{rr} = 1.0 \text{ mA}$ *UNLESS OTHERWISE SPECIFIED

